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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): NAITO et al.	Atty. Dkt.: 01-235
Serial No.: Unknown	Group Art Unit:
Filed: Concurrently herewith	Examiner:
Title: MANUFACTURING METHOD OF SILICON CARBIDE SINGLE CRYSTALS	



Assistant Commissioner for Patents
Washington, D.C. 20231

Date: December 10, 2001

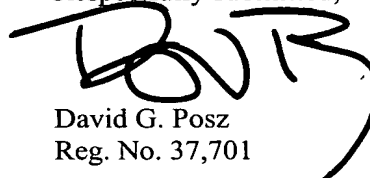
INFORMATION DISCLOSURE STATEMENT

Sir:

Pursuant to 37 C.F.R. §1.56, the reference(s) listed on the attached Form PTO-1449 is/are being submitted for consideration by the Examiner without any admission that it/they constitute(s) statutory prior art, or without any admission that it/they contain(s) subject matter that anticipates the invention or renders the invention obvious to a person of ordinary skill in the art.

The Examiner is requested to initial the attached PTO Form-1449 and to return a copy of same to the undersigned attorney as proof that the listed reference(s) has/have been considered and made of record.

Respectfully submitted,


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[JP-A-2000-34198]

An object is to provide a high productive manufacturing method of a large scale SiC single crystal which is at high purity and high quality, in such a way that crystal boundary, micro-pipe and the like are very few.

A β -SiC polycrystalline layer 2 is formed on a β -SiC single crystal substrate 1 by thermal CVD method to form composite M. The composite M is subjected to thermal treatment at high temperature of 2100 to 2400 °C to recrystallize the β -SiC polycrystalline layer 2 to form a single crystal. As a result, α -SiC is grown large to be unified, which is composed of the single crystal and the β -SiC single crystal substrate 1 in which crystal axes are oriented same direction.